

What is claimed is:

1-7. (Cancelled)

8. (Original) A field effect transistor comprising:

a silicon substrate, wherein the top surface of said silicon substrate has an increased oxygen content when compared to other portions of said silicon substrate, and wherein said oxygen content of said top surface of said silicon substrate is below an amount that would prevent epitaxial growth;

an epitaxial silicon halo layer on said top of said silicon substrate;

an epitaxial silicon source/drain layer on said epitaxial silicon halo layer; and

a gate stack above said epitaxial silicon source/drain layer.

9. (Original) The field effect transistor in claim 8, wherein source/drain dopants are substantially limited to said epitaxial silicon source/drain layer.

10. (Original) The field effect transistor in claim 8, wherein said increased oxygen content substantially limits dopants within said epitaxial silicon layer from moving into said silicon substrate.

11. (Original) The field effect transistor in claim 8, wherein said silicon substrate includes a column portion extending through said epitaxial silicon panel layer and said epitaxial silicon source/drain layer, wherein said column portion is below said gate conductor.

12. (Original) The field effect transistor in claim 8, wherein halo dopants are substantially limited to said epitaxial silicon halo layer.

13. (Original) The field effect transistor in claim 8, further comprising isolation regions in said epitaxial silicon layer and said silicon substrate.

14. (Original) The field effect transistor in claim 8, further comprising sidewall spacers on said gate conductor.

15-34. (Cancelled).